



Automation of Die Attach of Si onto Cu using BondFlow™

IMAPS New England 44th Annual
Symposium & Expo
May 2, 2017

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Outline

- Summary of *BondFlow*
- Trends in Packaging of High Power Devices
- *BondFlow* experiment
- Results bonding to bare Al and to plated Cu
- Future investigations



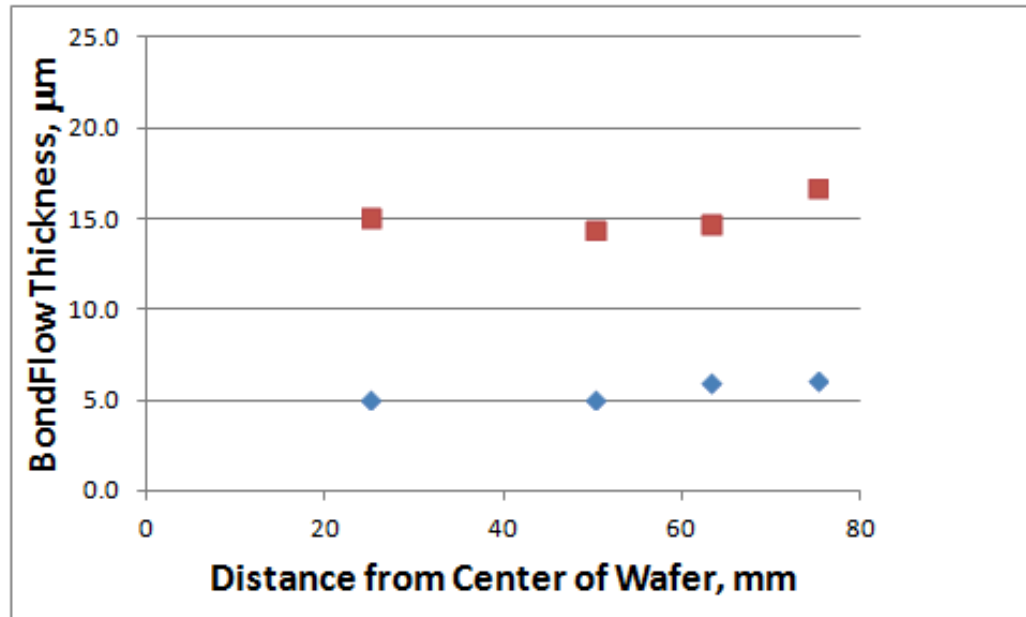
BOTTOM LINE on TPI Bondflow™

- Spin-coatable, backside die attach adhesive that bonds well to bare Al and to ENEPIG-plated Cu
- Durable bondlines between CTE-mismatched substrates, even Si-on-Al and Si-on-plated Cu
- Robust polyimide properties, including ductility (linear thermoplastic polymer vs cross-linked thermoset)
- Thin bondlines after cure (3 - 15 μm , with Ag-loading)
- Thermoplastic bonding process is very 'automatable', with short cycle times and high throughput
- B-staged BondFlow™ cures on a hot plate at 250°C after only 2 seconds under pressure
- Electrical resistivity of $<1\text{E-}4 \Omega\text{-cm}$.

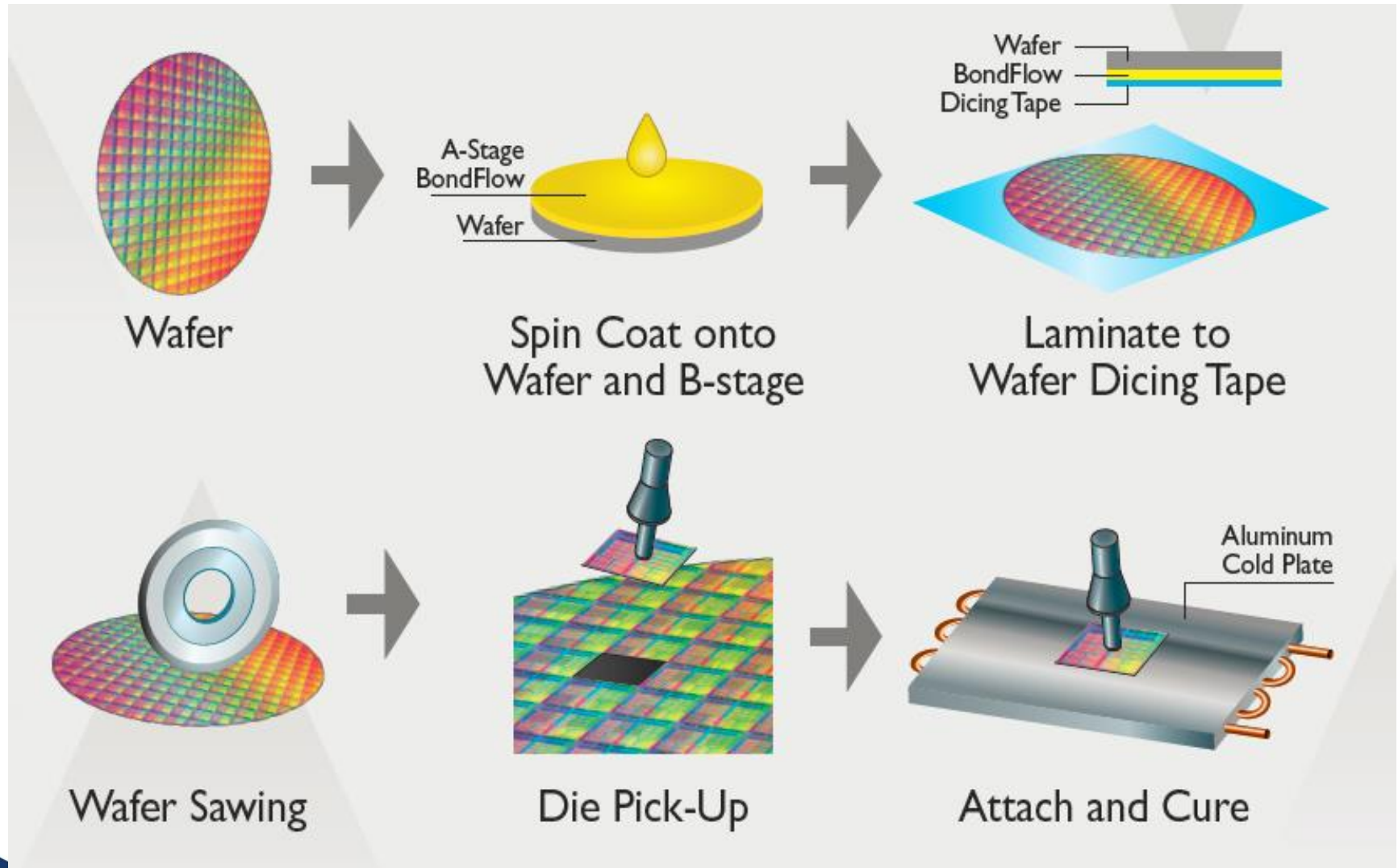


What is *BondFlow™*?

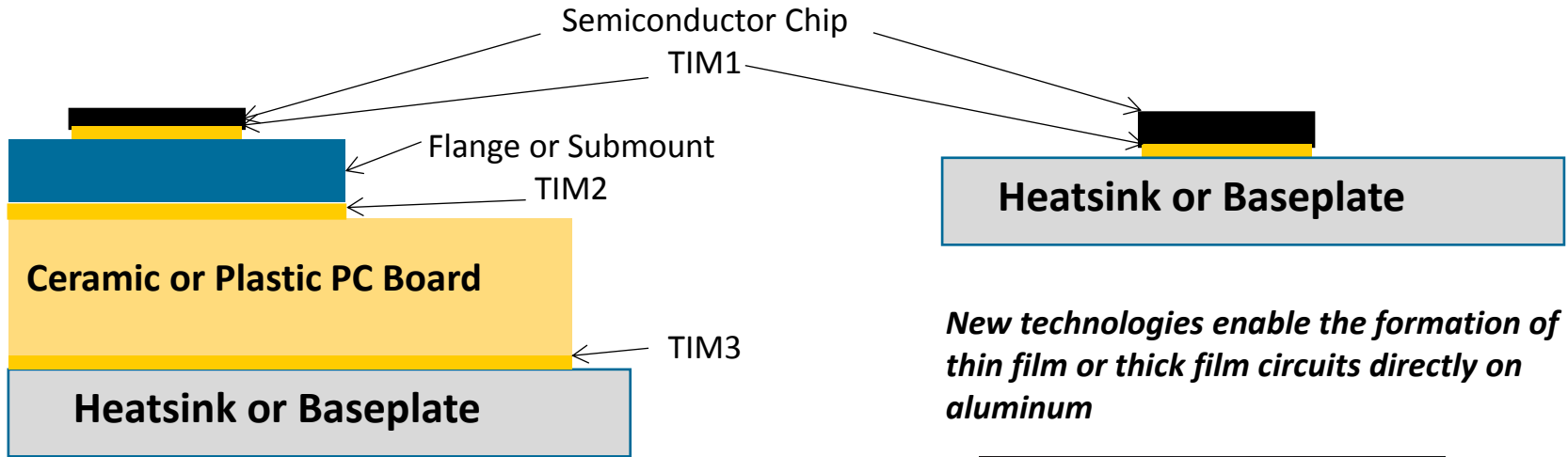
- BondFlow™ is A-Stage TPI filled with silver particles.
- BondFlow™ has a low enough viscosity to be deposited by spin coating or slot die coating.
- BondFlow™ can be B-staged into a non-tacky solid with a long shelf life at room temperature.
- BondFlow™ spin-coated coatings are very consistent



Process Flow with BondFlow™



Trend in Packaging: Reduce the Number of Layers!



New TIM1 die attach materials must strongly adhere to both the semiconductor chip (Si) and baseplate (Al) despite the severe mismatch in CTE.

New technologies enable the formation of thin film or thick film circuits directly on aluminum

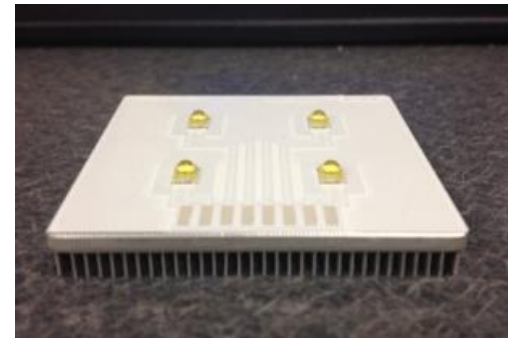
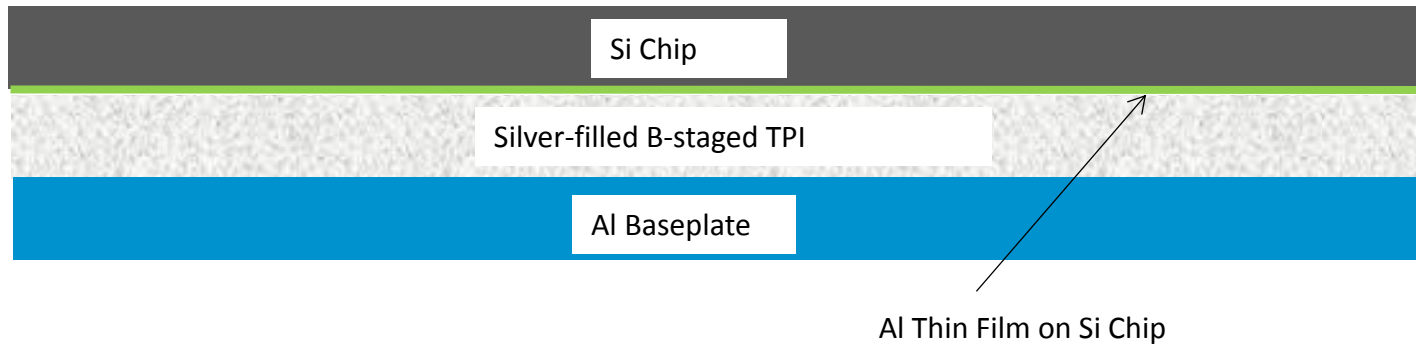


Image courtesy Heraeus Celcion



What is *BondFlow™*?



Schematic Cross Section (not to scale)

BondFlow can be tailored to the particular application by varying:

- viscosity
- thickness of B-staged coating
- weight % loading of silver particles in TPI



BondFlow™ can be Spun-On the Backside of a Wafer

1. Aluminum coated wafer backside
2. Spin on BondFlow
3. B-stage at 125-150°C in air
 - *Not tacky after B-staging*
4. Dice with diamond saw
 - *B-staged TPI can contact the dicing tape*
5. Pick and place dice from tape onto substrate heated on a hot stage
6. Apply pressure to cure at 250°C in air



Wafer Backside Spin Coating

- ▶ Silicon 150 mm Ø x 680 µm wafer with Aluminum metallization
- ▶ Diced into 3.6mm x 3.6mm squares

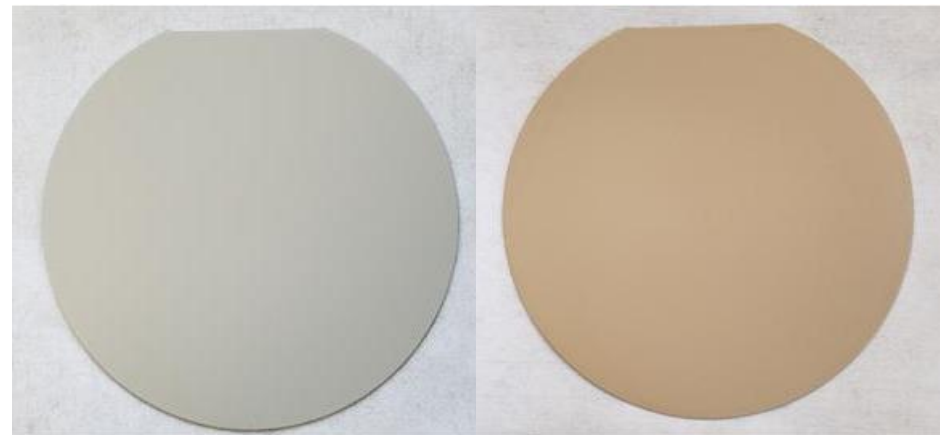
Wet (A-stage) spun coating on wafer
(reflection of brick wall visible on coating)



Wafer #	Wt % Ag in C-stage	RPM on Spin Coater	B-Stage thickness by mass, µm
668022 "1B"	80%	1500	6.7
668023 "4B"	80%	500	19.4

B-staged ~7 µm
Coating

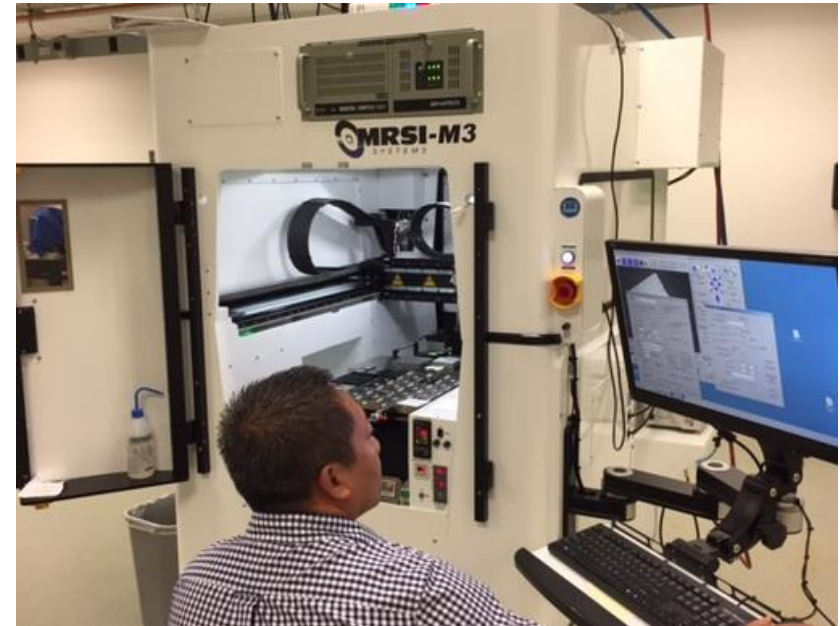
B-staged ~19 µm
Coating



▶ MRSI Systems *M-3* Automatic Die-Attach System

Capabilities

- ▶ Hot stage up to 500°C
- ▶ Pick and place to $\pm 3\mu\text{m}$
- ▶ Collet control
 - Programmable load
 - Scrub Option
- ▶ High speed, automatic operation
- ▶ Options:
 - Lift dice off the dicing tape
 - Tape-and-reel pick up and placement



BondFlow Automated Die Attach Investigation

Ø150mm Si wafer 680 µm (0.027”) thick

- ▶ Backside coated with 100nm Al
- ▶ Backside spun coat with Ag-filled BondFlow at 1500 and 500 RPM to produce 2 thicknesses
- ▶ B-staged in air at 150°C; 10 min. for thinnest and 20 min. for thickest coating
- ▶ Diced into 3.6mm x 3.6mm squares

BondFlow:

- ▶ 80 wt% Ag
- ▶ Two grades of Ag evaluated
- ▶ Viscosity = 9800 cP at 24°C with a Thixotropic index of 2

Substrate:

- ▶ Al 6061 plates 1” x 0.7” x 0.125” (Surface $R_a = 0.05 \mu\text{m}$)
- ▶ Surface prep: wiped with isopropanol

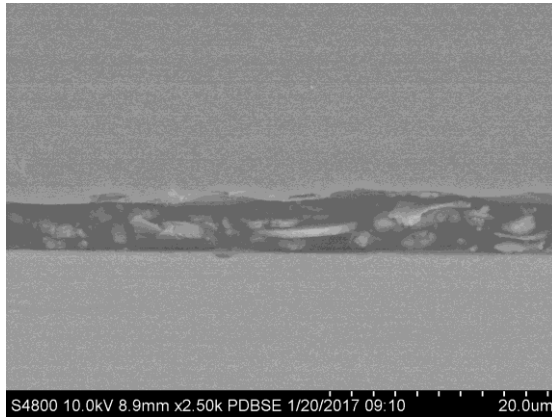
Die attached & Cure in the MRSI M-3 Die or 705 Attach System

- ▶ Four dice per substrate
- ▶ Heat substrate on hot plate at 250°C for 20 – 85 seconds
- ▶ Bond each die under pressure for 2 seconds
- ▶ Pressure of 188, 376, 750 or 1128 kPa (250, 500, 1000 and 1500 gf)

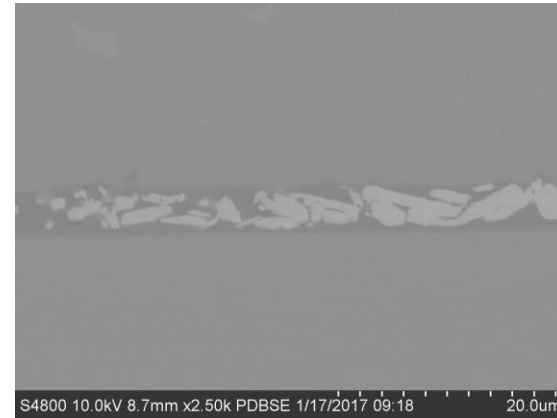


BondFlow Cross-Section Micrographs

Thin Bondline

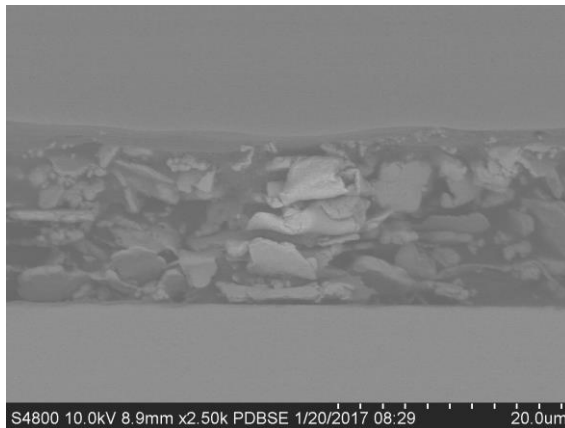


SEM of as-sawn cross-section of B-staged BondFlow on Si die.

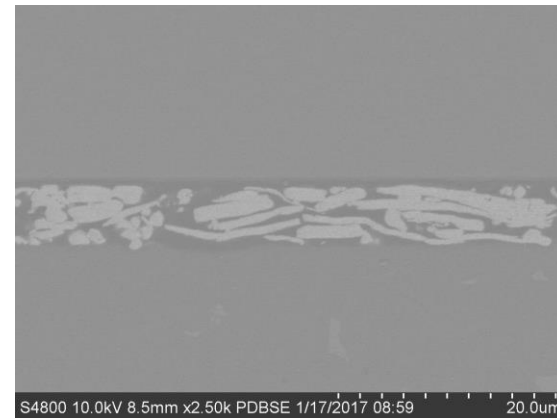


SEM of polished cross-section of cured BondFlow bonding Si to Al

Thick Bondline



SEM of as-sawn cross-section of B-staged BondFlow on Si die.



SEM of polished cross-section of cured BondFlow bonding Si to Al

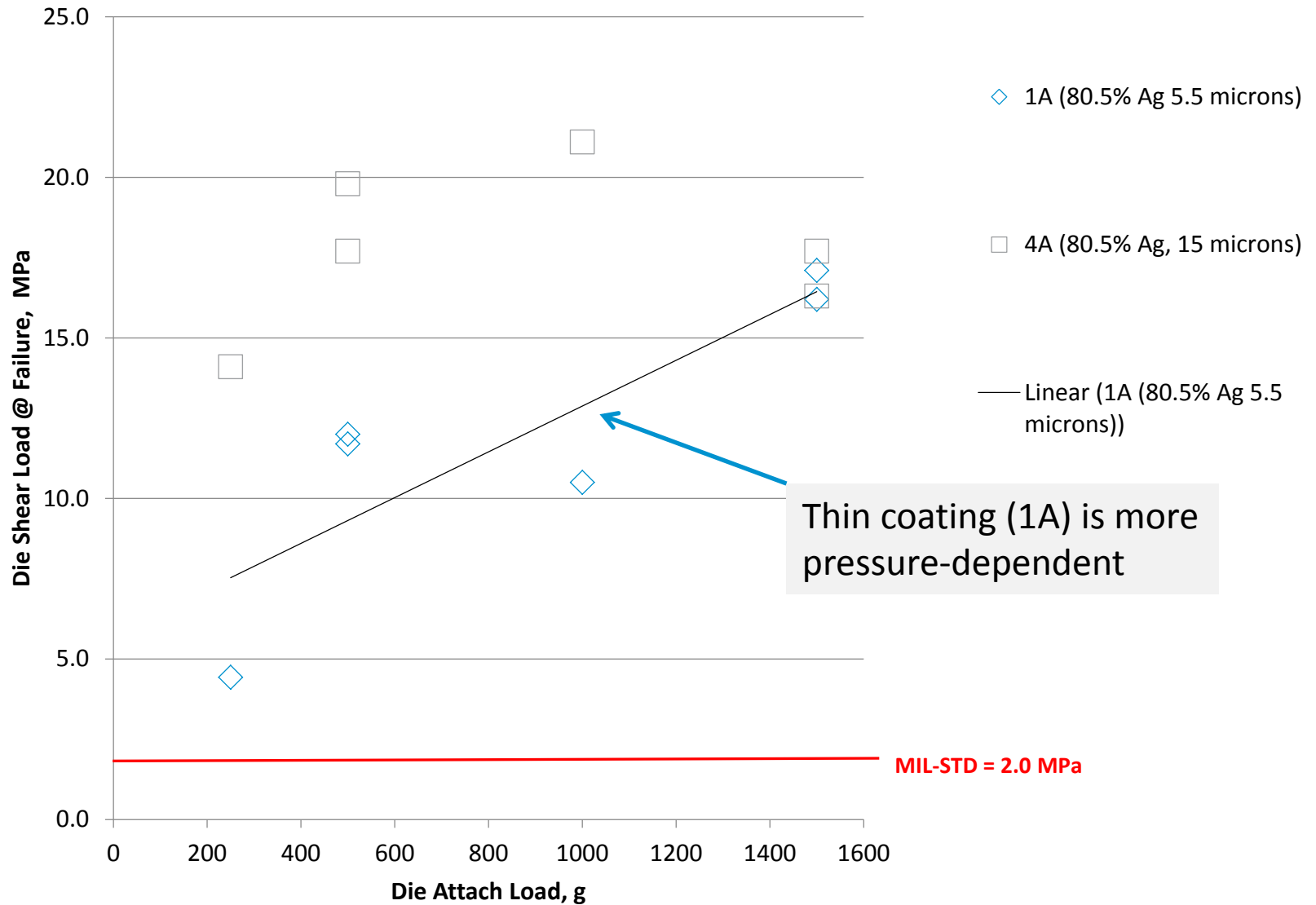


Summary of Coating Conditions

- Aluminum metallized Silicon wafers
- Each die under pressure for 2 seconds: 250, 500, 1000 or 1500 gf (27, 54, 108 and 162 psi or 188, 376, 750 and 1128 kPa.)
- Thickness measured after B-stage: $\sim 5 \mu\text{m}$ and $\sim 15 \mu\text{m}$
- Thickness measured after cure: $4.7 \mu\text{m}$ and $6.2 \mu\text{m}$
- Reduction in thickness after cure was greater for the thicker B-staged layer



BondFlow Die Shear Results



BondFlow Die Shear Images

Thin BondFlow (~5 μm)

Thick BondFlow (~15 μm)

High Ag Loading (~80 wt%)

High Bond Load (1500 g)
Shear 16.2 ± 3.7 MPa



Low Bond Load (250 g)
Shear 14.4 ± 2.7 MPa



High Bond Load (1500 g)
Shear 17.6 ± 7.8 MPa



Low Bond Load (250 g)
Shear 14.1 ± 5.2 MPa



Next Experiments: Investigate Effects of Ag Loading and Substrate Material

Substrates

- ▶ Al-coated Si
- ▶ Alumina
- ▶ BondFlow B-staged onto the Substrate
- ▶ Diced into 3.6 mm x 3.6 mm squares

BondFlow:

- ▶ 80 wt% Ag
- ▶ Two grades of Ag evaluated
- ▶ Viscosity = 9800 cP at 24°C with a Thixotropic index of 2

Substrate:

- ▶ Eless Ni + Eless Pd + Immersion Au plated copper 1" x 0.7" x 0.06"
- ▶ Al 6061 plates 1" x 0.7" x 0.125" (Surface $R_a = 0.05 \mu\text{m}$)
- ▶ Surface prep: wiped with isopropanol

Die attached & Cure in Manual Hydraulic Press

- 100 psi (690 kPa) per die
- 3 - 5 minutes at 250°C



BondFlow Formulation & Characterization

BondFlow Formulation: 80 wt% Ag lot 667960-2 NP-771-17-2

Composition checked by LOI at 800C wt% Ag = 80.8 wt % (80.2% target)

Viscosity measured using Brookfield RVT viscometer with Spindle RV3

Adhesion Strength measured by bonding Al₂O₃ dice (3.6mm x 3.6 mm x 1 mm) to ENEPIG plated Cu coated with 667960-2 BondFlow (MIL-STD-883 Method 2019.7)

Volume electrical resistivity measured by Four Point Probe (MIL STD 883 Method 5011.4)

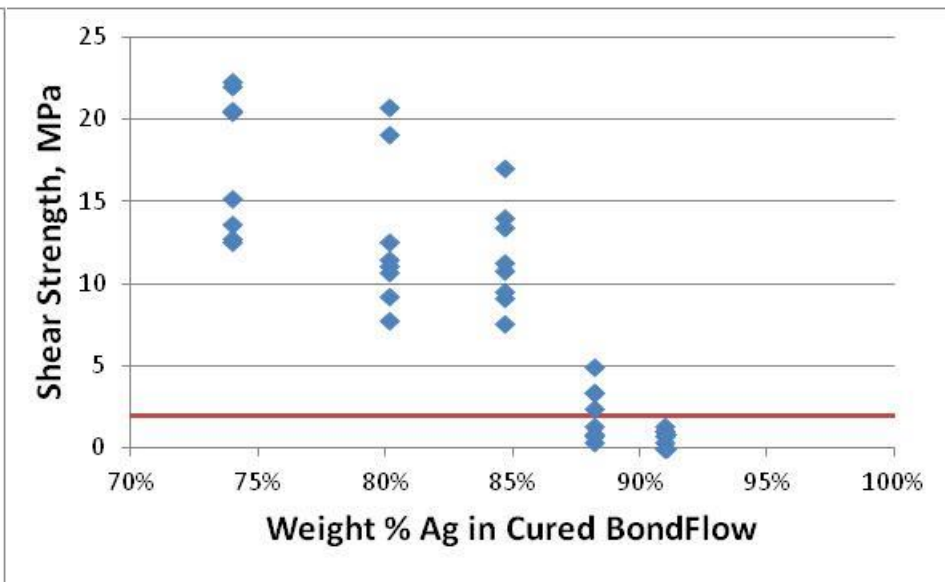
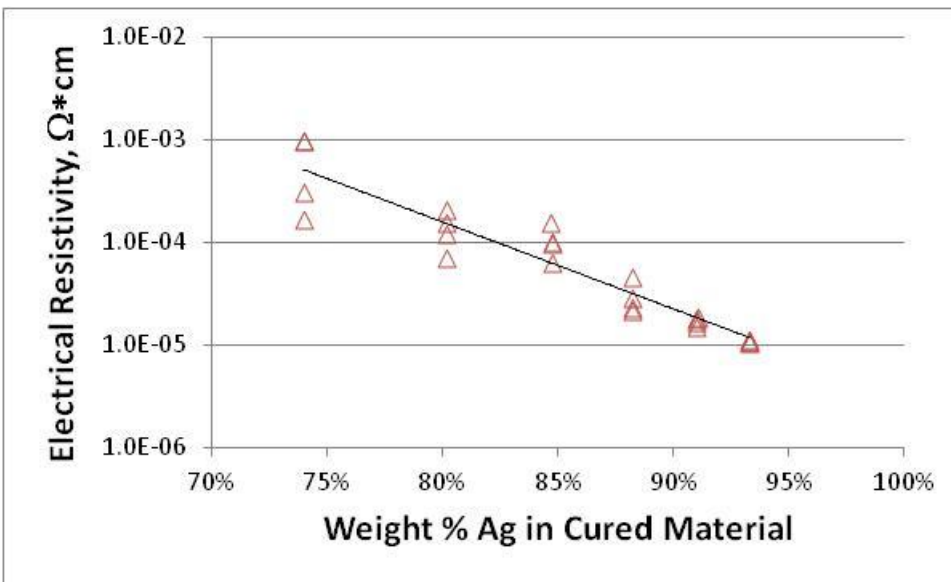
667960-2 80 wt% Ag BondFlow	
RPM	Viscosity, cP
1	14,200
2.5	10,000
5	8,140
10	6,900
Average	9,810
Thixotropic Index	2.06
Temperature, °C	24

RVT Viscometer
Measurement: BondFlow is
Thixotropic



Resistivity and Adhesion Strength vs Ag %

- Electrical resistivity decreases with increasing Ag
- Bond strength is acceptable until > 85 wt% Ag where a drop in strength is observed



Die-Shear Strength

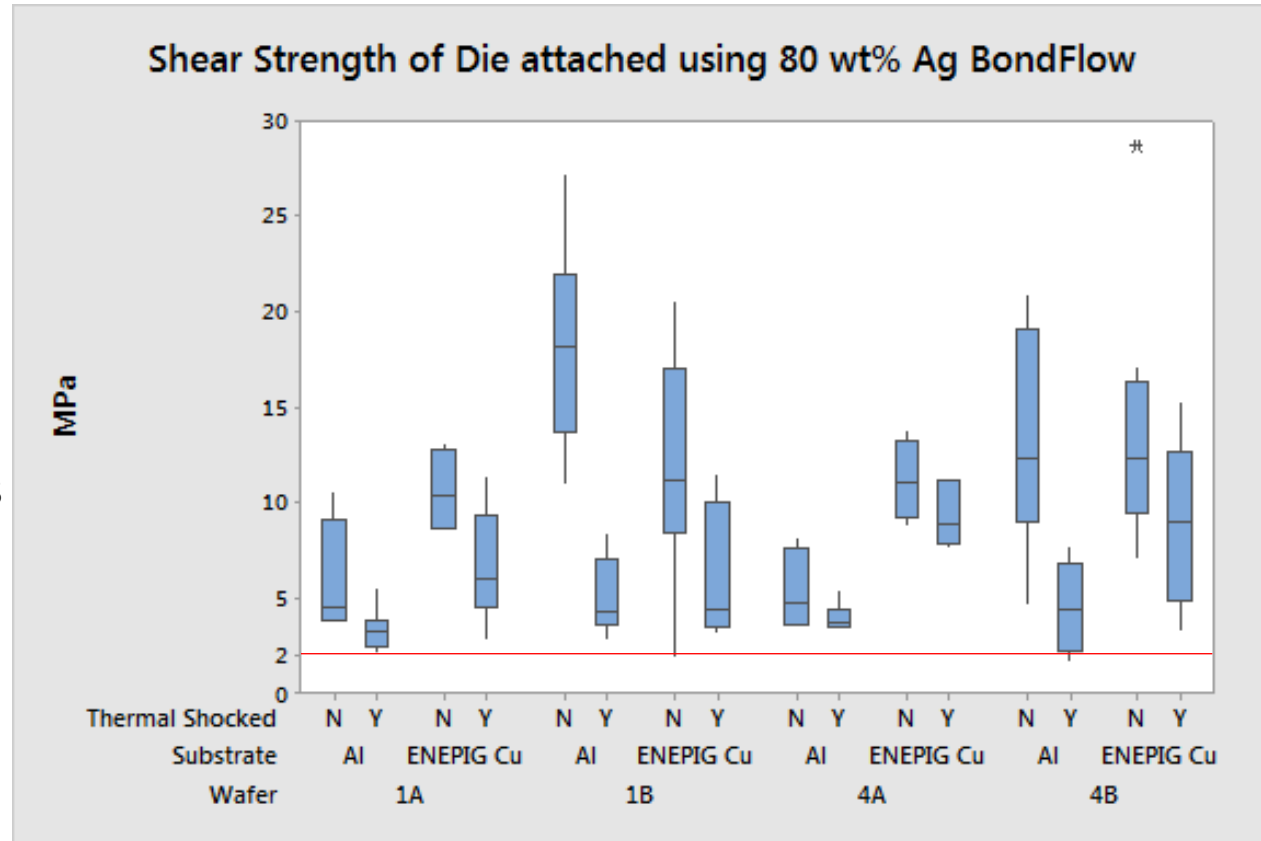
- Manual Die attach using laboratory heated platen press
- Bonding of 3.6mm x 3.6mm Silicon die coated with BondFlow

Wafer	Thickness, μm	Ag Grade
1A	5	A
1B	7	B
4A	15	A
4B	19	B

Bonded @ 250°C for 3 minutes

Thermal Shock Process:

Remove from 250°C hot platen and place on RT Aluminum Block with water on top; quickly cools to RT. Repeated 10X



Conclusions: Adhesion strength to ENEPIG Cu retains its strength better after thermal Shock than adhesion strength to Aluminum; likely due to lower CTE mismatch.



Bond Strength Retention after Severe Thermal Shocks

250°C => 25°C in 1 second... 10X

Die-shear loss with Thermal Shock		
	----- Substrate -----	
Coating	ENEPIG Cu	Al
1A	38%	43%
1B	50%	72%
4A	17%	26%
4B	33%	66%

RESULT: *Plated copper retains die-shear strength more than aluminum, likely due to lower CTE-mismatch.*



Electrical Resistivity of a 80 wt% Cured BondFlow with Silver Particles

Measured by 4-Point Probe per MIL-STD 883 Method 5011

Volume resistivity $\rho < 1E-4 \Omega\text{-cm}$

This volume resistivity is similar to most silver-filled die-attach epoxies



Volume Resistivity Measurement Setup

- ▶ 4 wire (4 point) mode. Average of at least 100 data points.



Discussion

- BondFlow is a user-friendly adhesive that can be spin-coated onto Al metallized Si wafers and then B-staged.
- Since B-staged BondFlow is not tacky, it can be placed onto dicing tape to enable automated die attach. Shelf life of B-staged film at room temperature is several years.
- Curing can be achieved onto a Al substrate heated to 250°C after only 2 seconds under pressure. Curing is complete on the hot stage; no need to pass the part through a curing oven.
- All samples examined exceeded the MIL-STD die shear specification of 5.5 lbs (2 MPa or 289 psi) despite the large CTE difference between Si and Al, and between Si and Cu.
- Degradation of shear strength after thermal shock was less for Si-on-Cu than for Si-on-Al.



Dielectric BondFlow Also Available

- ▶ Filled with thermally conductive ceramic particles
- ▶ Can be spin-coated
- ▶ Die shear strength exceeds MIL-STD-883 Method 2019.7
- ▶ Thermal conductivity ~ 1 W/m-K
- ▶ Dielectric strength 140 V/ μm
 - By comparison, dielectric strength of 96% alumina is 8.3 V/ μm



Potential Applications

- Die attach of high power Si, GaAs or SiC dice to
 - Al or Cu heatsinks
 - Ceramic heatsinks
 - Diamond
 - Metal matrix composites
- High-temperature electronics
- Stacked dice, System In Package (SIP)
- TIM2 applications: e.g., LED submounts onto Al heatsinks

- *Any others??*



Future Investigations

- ▶ Measure thermal conductivity
- ▶ Additional temperature cycle air-to-air per MIL-STD-883 1010.8 (-65°C to +150°C)
- ▶ C-SAM imaging of bondline

Please provide your suggestions!



Special Thanks to:

- ▶ Jack Inocencio, Julius Ortega, John Hayes, Jon Medernach and Michael Chalsen

MRSI Systems

- ▶ Kazoua Lor, Dennis Hoefs and Jayne Spanos

Materion



Future Investigations

- ▶ Measure thermal conductivity
- ▶ Additional temperature cycle air-to-air per MIL-STD-883 1010.8 (-65°C to +150°C)
- ▶ Thermal soak at 175°C for 1000 hrs.

Please provide your suggestions!



Thank you!

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